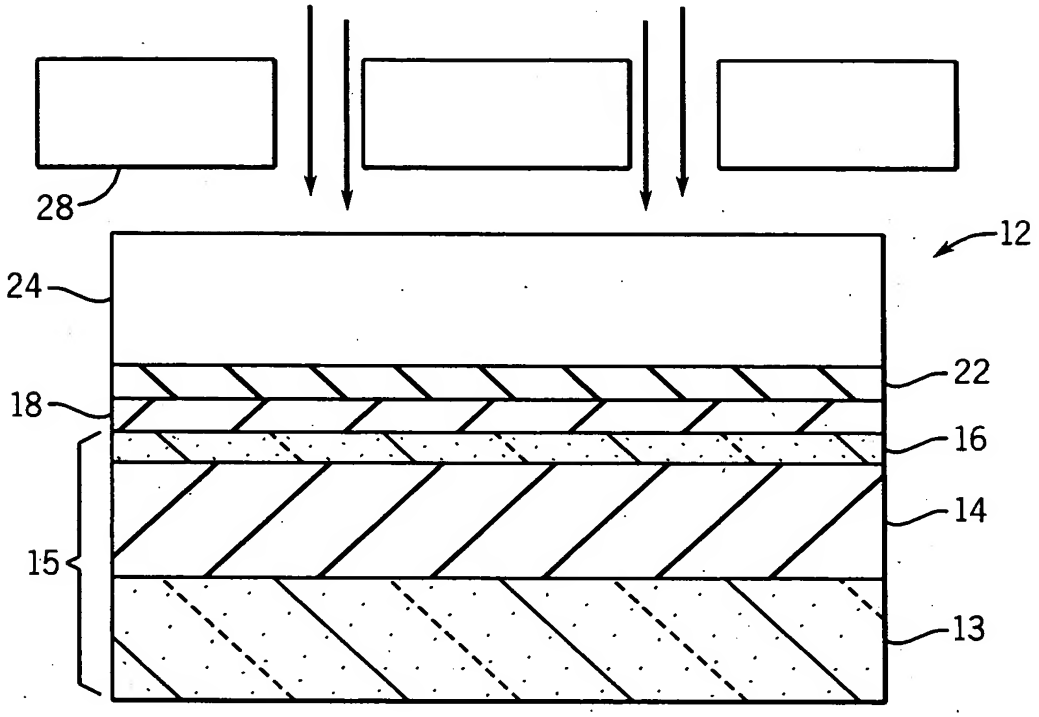

FIG. 1

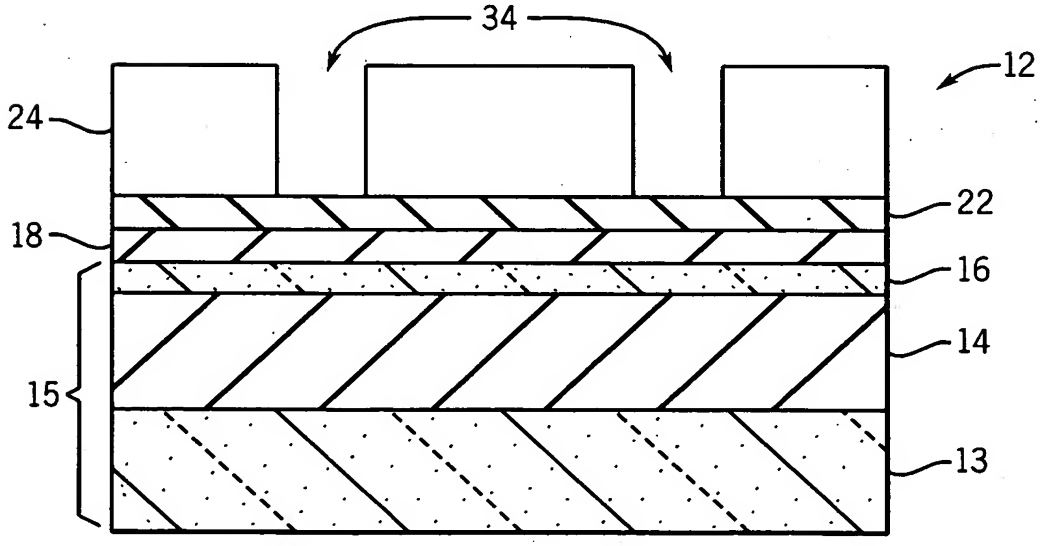

FIG. 2

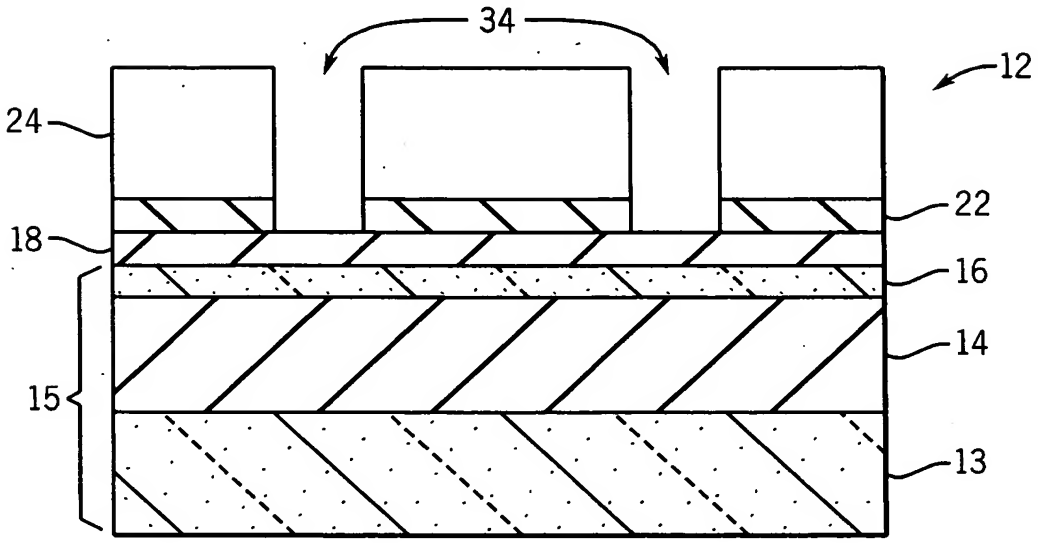

FIG. 3

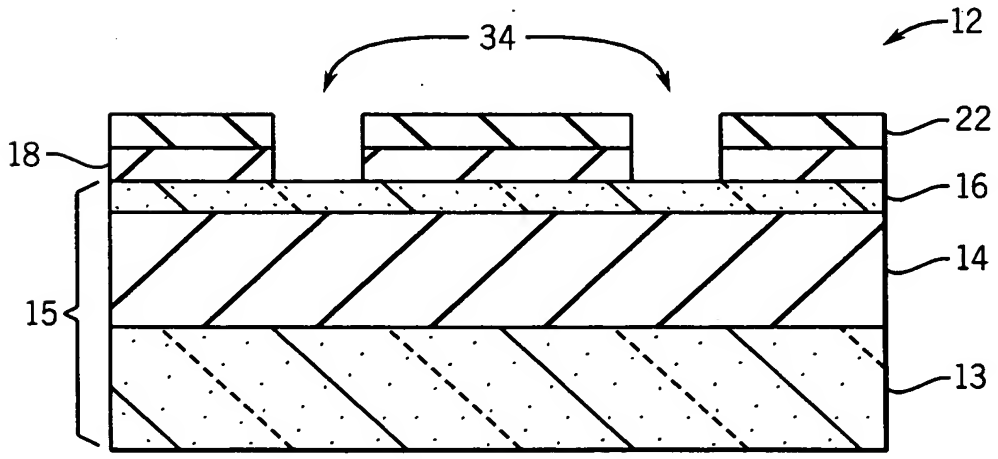

FIG. 4

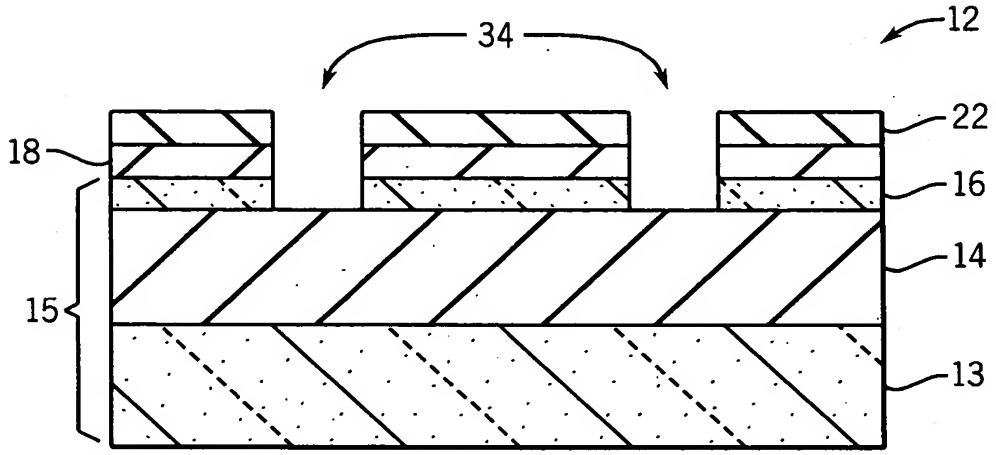

FIG. 5

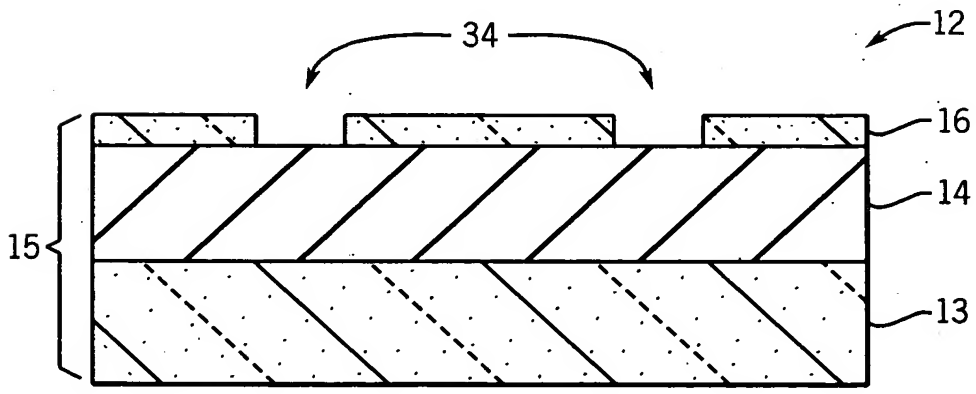

FIG. 6

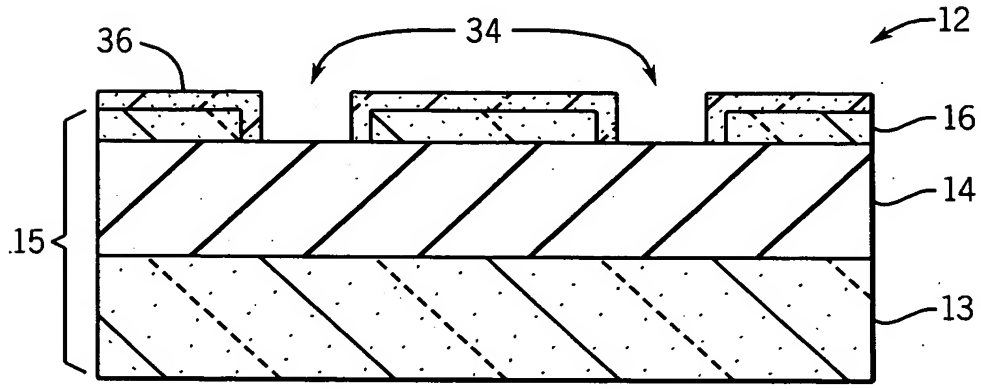

FIG. 7

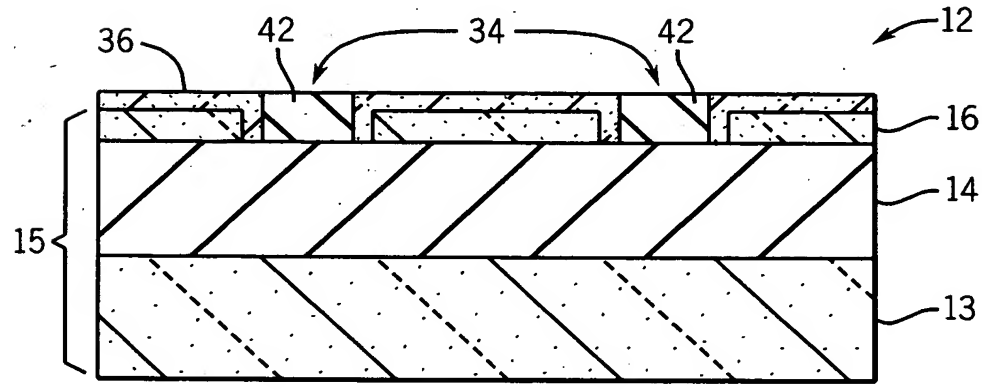

FIG. 8

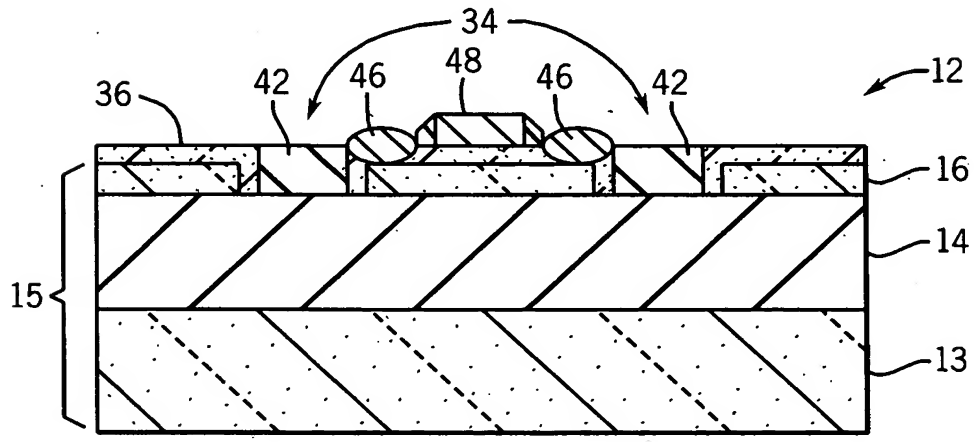
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FIG. 9

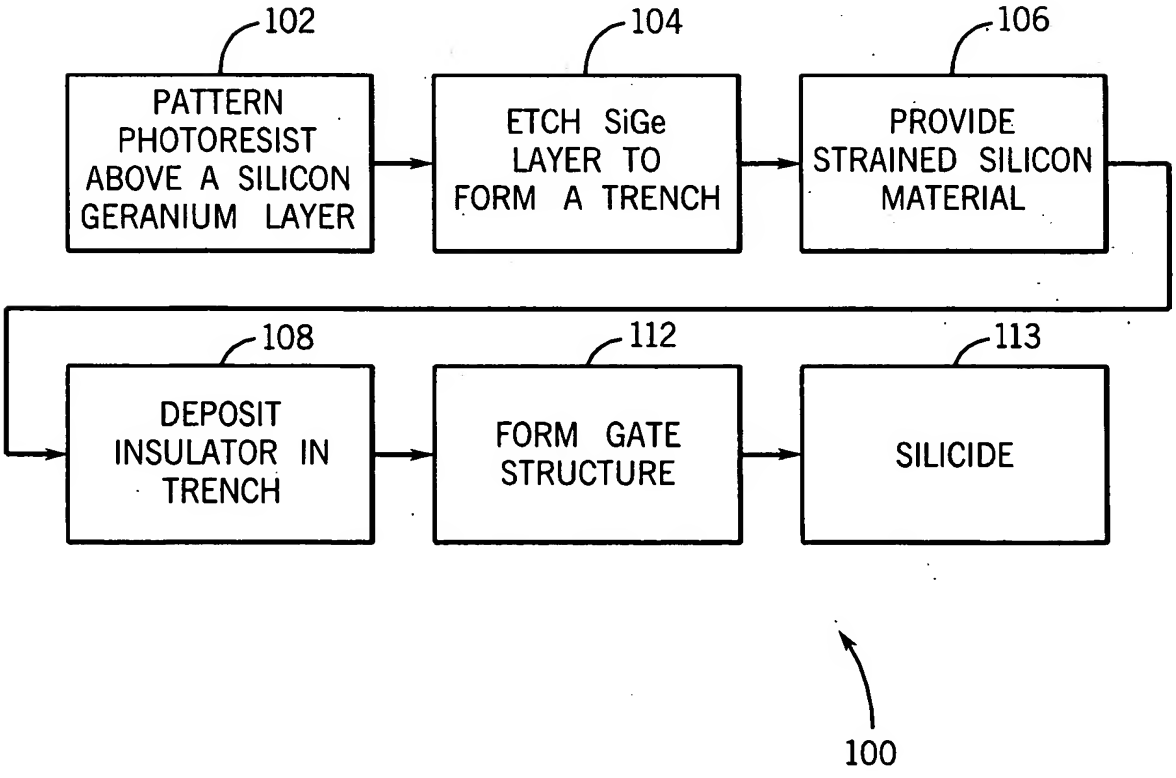
102
PATTERN PHOTORESIST ABOVE A SILICON GERANIUM LAYER
104
ETCH SiGe LAYER TO FORM A TRENCH
106
PROVIDE STRAINED SILICON MATERIAL
108
DEPOSIT INSULATOR IN TRENCH
112
FORM GATE STRUCTURE
113
SILICIDE
100

FIG. 10

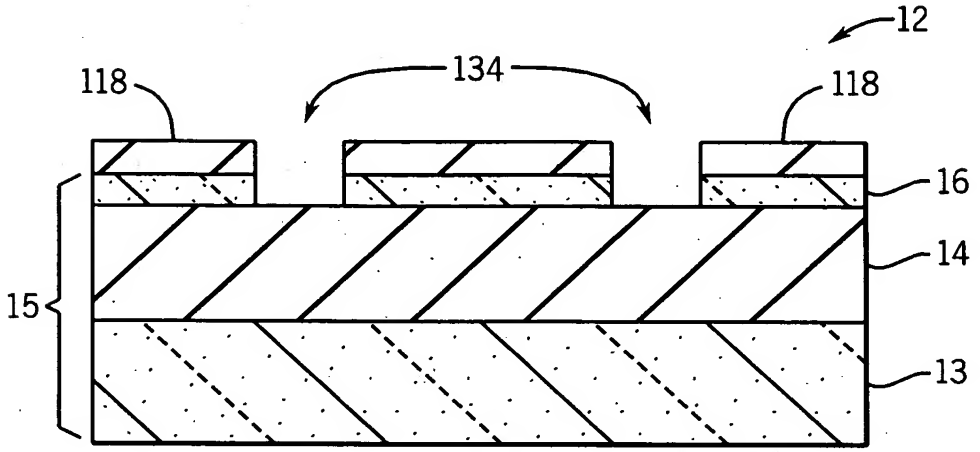

FIG. 11

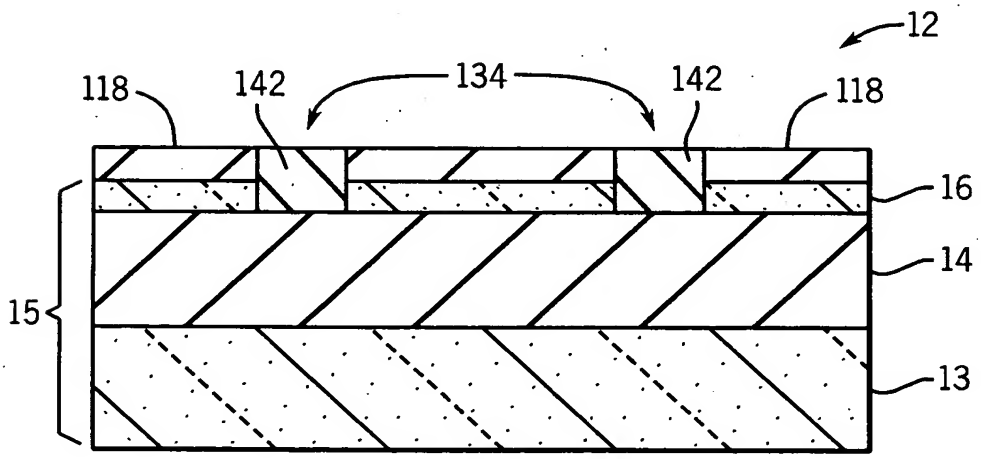

FIG. 12

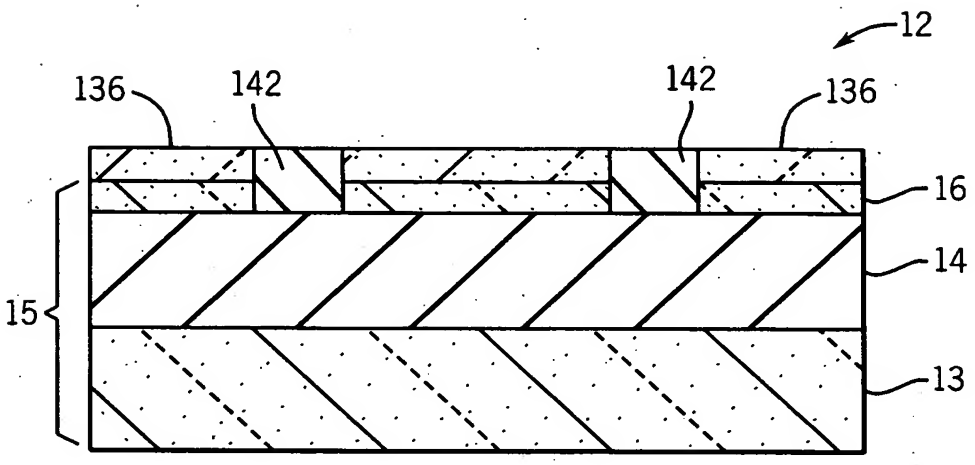

FIG. 13

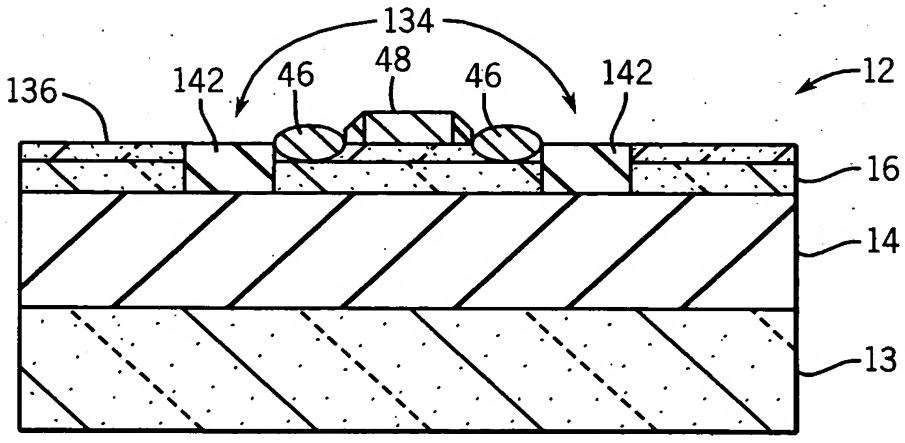

FIG. 14

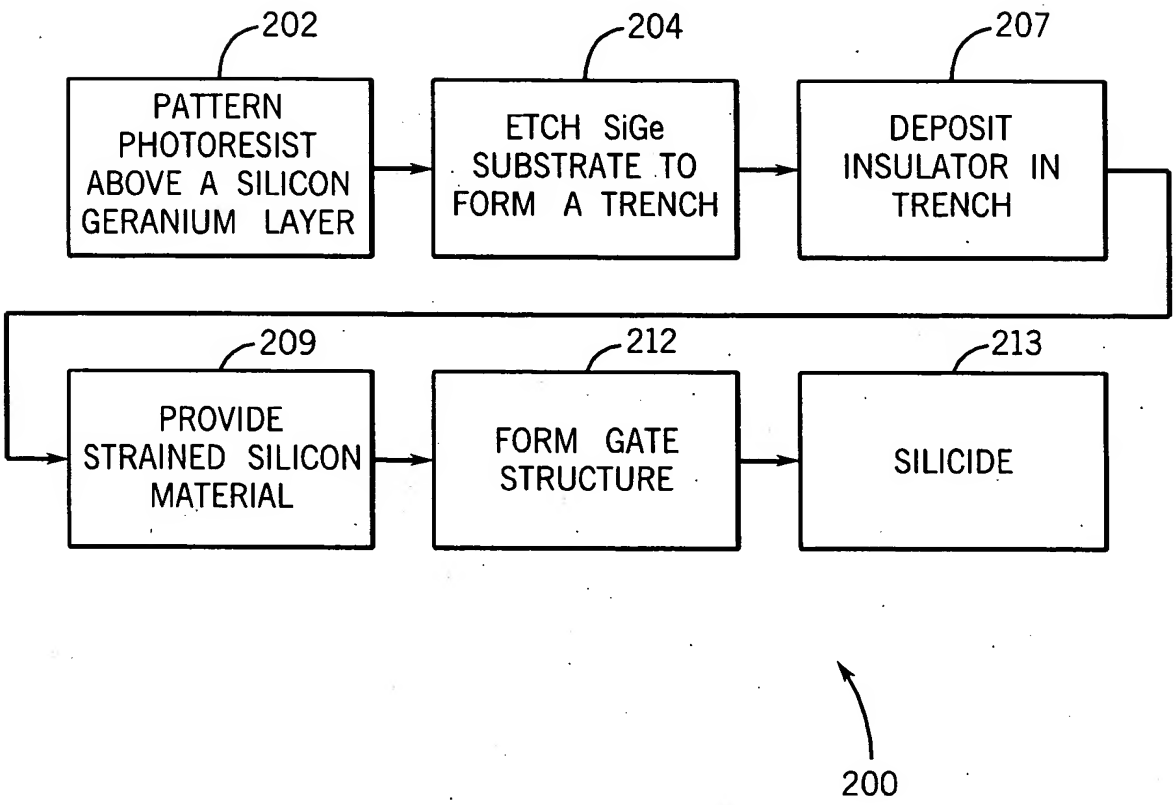
202
PATTERN PHOTORESIST ABOVE A SILICON GERANIUM LAYER
204
ETCH SiGe SUBSTRATE TO FORM A TRENCH
207
DEPOSIT INSULATOR IN TRENCH
209
PROVIDE STRAINED SILICON MATERIAL
212
FORM GATE STRUCTURE
213
SILICIDE
200

FIG. 15